

Ming Gao

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

17
papers

112
citations

6
h-index

10
g-index

19
ext. papers

128
ext. citations

4.2
avg, IF

2.22
L-index

#	Paper	IF	Citations
17	Low Drift Reference-less ISFET Comprising Two Graphene Films with Different Engineered Sensitivities. <i>ACS Applied Electronic Materials</i> , 2022 , 4, 416-423	4	0
16	The hole transport mechanism of MoO _x /a-Si: H(i)/n-Si heterojunction photovoltaic devices: the source of the S-shaped behavior. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 425302	3	1
15	Temperature-dependent nonmonotonous evolution of excitonic blue luminescence and Stokes shift in chlorine-based organometallic halide perovskite film. <i>Applied Physics Letters</i> , 2020 , 116, 072104	3.4	0
14	Improvement of the performance of ITO/a-SiO _x /n-Si device by controllable sputtering power and reducible interface states. <i>Materials Science in Semiconductor Processing</i> , 2020 , 105, 104702	4.3	2
13	First principle study of formation mechanism of molybdenum-doped amorphous silica in MoO ₃ /Si interface. <i>Wuli Xuebao/Acta Physica Sinica</i> , 2019 , 68, 103101	0.6	1
12	Electronic structure of molybdenum-involved amorphous silica buffer layer in MoO _x /n-Si heterojunction. <i>Applied Surface Science</i> , 2019 , 473, 20-24	6.7	5
11	Role of nuclei in controllable MoS ₂ growth by modified chemical vapor deposition. <i>Journal of Materials Science: Materials in Electronics</i> , 2018 , 29, 7425-7434	2.1	2
10	Bifunctional Hybrid a-SiO (Mo) Layer for Hole-Selective and Interface Passivation of Highly Efficient MoO ₃ /a-SiO (Mo)/n-Si Heterojunction Photovoltaic Device. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 27454-27464	9.5	21
9	Effect of post-annealing on the properties of thermally evaporated molybdenum oxide films: Interdependence of work function and oxygen to molybdenum ratio. <i>Materials Science in Semiconductor Processing</i> , 2018 , 75, 166-172	4.3	26
8	Effective Passivation and Tunneling Hybrid a-SiO(In) Layer in ITO/n-Si Heterojunction Photovoltaic Device. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 17565-17575	9.5	14
7	Variation of passivation behavior induced by sputtered energetic particles and thermal annealing for ITO/SiO _x /Si system. <i>Chinese Physics B</i> , 2017 , 26, 045201	1.2	9
6	Questing and the application for silicon based ternary compound within ultra-thin layer of SIS intermediate region. <i>Applied Surface Science</i> , 2016 , 388, 57-63	6.7	4
5	Elucidating the evolution of the current-voltage characteristics of planar organometal halide perovskite solar cells to an S-shape at low temperature. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 157, 981-988	6.4	12
4	Hydrogen-free synthesis of few-layer graphene film on different substrates by plasma enhanced chemical vapor deposition. <i>Journal of Materials Science: Materials in Electronics</i> , 2015 , 26, 6961-6969	2.1	2
3	Hydrogen-free synthesis of graphene/graphitic films directly on Si substrate by plasma enhanced chemical vapor deposition. <i>Journal of Materials Science: Materials in Electronics</i> , 2015 , 26, 1485-1493	2.1	9
2	?????????????????????. <i>Chinese Science Bulletin</i> , 2015 , 60, 1841-1848	2.9	2
1	CVD Polycrystalline Graphene as Sensing Film of Extended-Gate ISFET for Low-Drift pH Sensor. <i>Journal of the Electrochemical Society</i> ,	3.9	2

